Elektronische Bauelemente

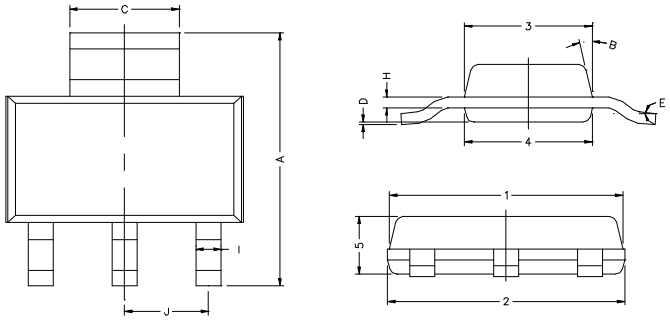
PZT3019

NPN Transistor

Epitaxial Planar Transistor

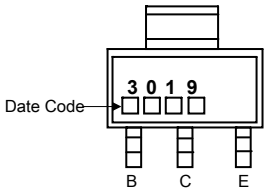
RoHS Compliant Product

SOT-223



Description

The PZT3019 is designed for general purpose amplifier applications and switching requiring collector currents 1A.



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.70	7.30	B	13°TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80

ABSOLUTE MAXIMUM RATINGS Ta=25°C

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	140	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current	1	A
P_D	Total Power Dissipation	2	W
T_J,T_{stg}	Junction and Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS Tamb=25°C unless otherwise specified

Parameter	Symbol	Min	Typ.	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV_{CBO}	140	-	-	V	I_C=100μA
Collector-Emitter Breakdown Voltage	BV_{CEO}	80	-	-	V	I_C=30mA
Emitter-Base Breakdown Voltage	BV_{EBO}	7	-	-	V	I_E=100 μA
Collector-Base Cutoff Current	I_{CBO}	-	-	50	nA	V_{CB}= 90V
Emitter-Base Cutoff Current	I_{EBO}	-	-	50	nA	V_{EB}=5V
Collector Saturation Voltage	V_{CE}(sat)	-	-	0.2	V	I_C=150mA,I_B=15mA
Base Saturation Voltage	V_{BE}(sat)	-	-	1.1	V	I_C=150mA,I_B=15mA
DC Current Gain	$h_{FE}1$	50	-	-		V_{CE}= 10V, I_C=0.1mA
	$h_{FE}2$	90	-	-		V_{CE}= 10V, I_C=10mA
	$h_{FE}3$	100	-	300		V_{CE}= 10V, I_C=150mA
	$h_{FE}4$	50	-	-		V_{CE}= 10V, I_C=500mA
	$h_{FE}5$	15	-	-		V_{CE}= 10V, I_C=1000mA
Gain-Bandwidth Product	fT	100	-	-	MHz	V_{CE}= 50mV, I_C= 50mA,f=100MHz
Output Capacitance	Cob	-	-	12	pF	V_{CB}= 10V, f=1MHz,I_E=0